EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	514	microcrystal$4 adj (layer film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 07:39
S2	6295	(deposit$4 inject$4) with intrinsic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 07:21
S3	100066	(deposit$4 inject$4) with plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 07:21
S4	839	concentration with diluent with gas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 07:26
S5	4	S1 and S2 and S3 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 07:27
S6	964	(concentration density) with diluent with gas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 07:26
S7	4	S1 and S2 and S3 and S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 07:38

S8	13	S2 and S3 and S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 07:38
S9	4	S8 and (microcrystal$4 adj (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 07:46
S10	0	S8 and (crystal$4 adj (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 07:39
S11	1	10/765,435	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 08:13
S12	2	("6274461").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 08:56
S13	1	11/017,187	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/20 08:57
S14	356	precursor with diluent with gas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/14 19:00
S15	161	@ad <= "20040127" and S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/14 19:00

S16	5075	((438/93) or (438/97) or (438/478) or (438/485) or (438/479) or (438/488) or (438/487)).CCLS.	US-PGPUB; USPAT	OR	OFF	2010/07/14 19:11
S17	10	S15 and S16	US-PGPUB; USPAT	OR	OFF	2010/07/14 19:12
S18	2908	(semiconductor or silicon) with material with (gas with mix$4)	US-PGPUB; USPAT	OR	ON	2010/10/05 19:14
S19	984	(chamber with (electromagnetic adj energy))	US-PGPUB; USPAT	OR	OFF	2010/10/05 19:15
S20	11	S18 and S19	US-PGPUB; USPAT	OR	OFF	2010/10/05 19:15
S21	9	S20 and microcrystalline	US-PGPUB; USPAT	OR	OFF	2010/10/05 19:16
S22	9	@ad <= "20040127" and S21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 19:16
S23	5	S22 and threshold	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 19:17
S24	0	S23 and ((varying or varied or vary or varies) with concentration)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 19:17
S25	204209	((varying or varied or vary or varies) with concentration)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 19:18
S26	169593	(semiconductor or silicon) with material with substrate	US-PGPUB; USPAT	OR	ON	2010/10/05 19:18
S27	8231	S25 and S26	US-PGPUB; USPAT	OR	ON	2010/10/05 19:18
S28	84908	(chamber with substrate)	US-PGPUB; USPAT	OR	OFF	2010/10/05 19:19
S29	1755	S27 and S28	US-PGPUB; USPAT	OR	OFF	2010/10/05 19:19

S30	387	S29 and parameter	US-PGPUB; USPAT	OR	OFF	2010/10/05 19:19
S31	27	S30 and (electromagnetic adj energy)	US-PGPUB; USPAT	OR	OFF	2010/10/05 19:20
S32	27	S31 and gas	US-PGPUB; USPAT	OR	OFF	2010/10/05 19:20
S33	27	S32 and pressure	US-PGPUB; USPAT	OR	OFF	2010/10/05 19:21
S34	0	S33 and (power adj density)	US-PGPUB; USPAT	OR	OFF	2010/10/05 19:21
S35	27	S33 and ((varying or varied or vary or varies) with concentration)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 19:21
S36	14	S35 and threshold	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 19:22
S37	11	S36 and (amorphous or microcrystalline)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 19:26
S38	1	10/765,435	US-PGPUB; USPAT	OR	OFF	2010/10/05 20:43
S39	5600	((438/93) or (438/96-97) or (438/478) or (438/485) or (438/479) or (438/488) or (438/487)).CCLS.	US-PGPUB; USPAT	OR	OFF	2010/10/05 21:49
S40	345	S39 and ((varying or varied or vary or varies) with concentration)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 21:54
S41	184	@ad <= "20040127" and S40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 21:54

S42	17	S41 and (threshold with (amorphous or microcrystalline or parameter$2 or material))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 21:58
S43	204209	((varying or varied or vary or varies) with concentration)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 21:58
S44	169593	(semiconductor or silicon) with material with substrate	US-PGPUB; USPAT	OR	ON	2010/10/05 21:58
S45	8231	S43 and S44	US-PGPUB; USPAT	OR	ON	2010/10/05 21:58
S46	84908	(chamber with substrate)	US-PGPUB; USPAT	OR	OFF	2010/10/05 21:58
S47	1755	S45 and S46	US-PGPUB; USPAT	OR	OFF	2010/10/05 21:58
S48	387	S47 and parameter	US-PGPUB; USPAT	OR	OFF	2010/10/05 21:58
S49	27	S48 and (electromagnetic adj energy)	US-PGPUB; USPAT	OR	OFF	2010/10/05 21:58
S50	27	S49 and gas	US-PGPUB; USPAT	OR	OFF	2010/10/05 21:58
S51	27	S50 and pressure	US-PGPUB; USPAT	OR	OFF	2010/10/05 21:58
S52	27	S51 and ((varying or varied or vary or varies) with concentration)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 21:58
S53	14	S52 and threshold	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 21:58
S54	11	S53 and (amorphous or microcrystalline)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 21:58
S55	17	S42 not S54	US-PGPUB; USPAT	OR	ON	2010/10/05 22:00

S56	3	S55 and (threshold with parameter$2)	US-PGPUB; USPAT	OR	ON	2010/10/05 22:08
S57	52	(subhendu near guha). in.	US-PGPUB; USPAT	OR	ON	2010/10/05 22:23
S58	9	S57 and (threshold with parameter$2)	US-PGPUB; USPAT	OR	ON	2010/10/05 22:24
S59	9	@ad <= "20040127" and S58	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 22:24
S60	2	S59 and S43	US-PGPUB; USPAT	OR	OFF	2010/10/05 22:24
S61	412	(Chi near2 Yang).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 22:25
S62	5	S61 and (threshold with parameter$2)	US-PGPUB; USPAT	OR	ON	2010/10/05 22:25
S63	4	@ad <= "20040127" and S62	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 22:26
S64	2	S63 and S43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 22:26
S65	4	(baojie near yan).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 22:30
S66	1	@ad <= "20040127" and S65	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/10/05 22:31

10/8/10 4:41:05 PM
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